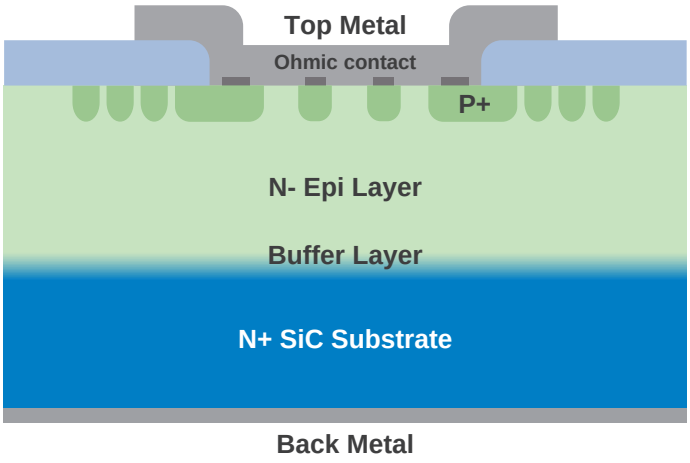
SiC Schottky Barrier Diode

For the Excellence in System Design

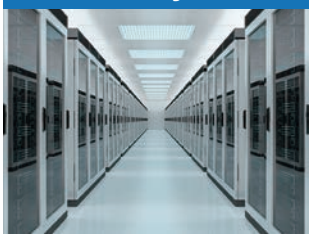
Features

- Low conduction loss
- Zero reverse recovery
- Temperature independent switching
- High surge current capability
- High ruggedness
- High junction temperature 175°C



Target Application

Power System



- Server Power
- Telecom Power
- PC Power

Green Energy

- PV Inverter
- ESS / BMS

Industrial

- EV Charging Pile
- UPS
- Industrial Motor

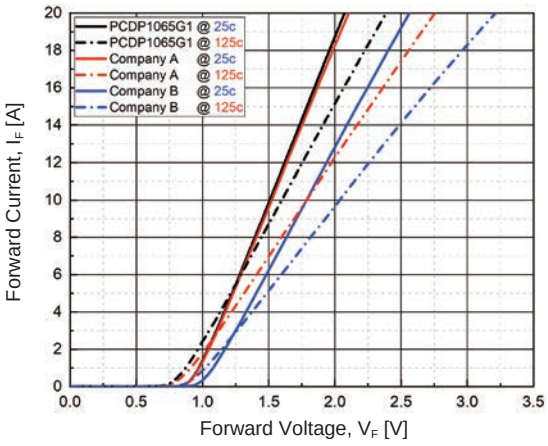
Consumer

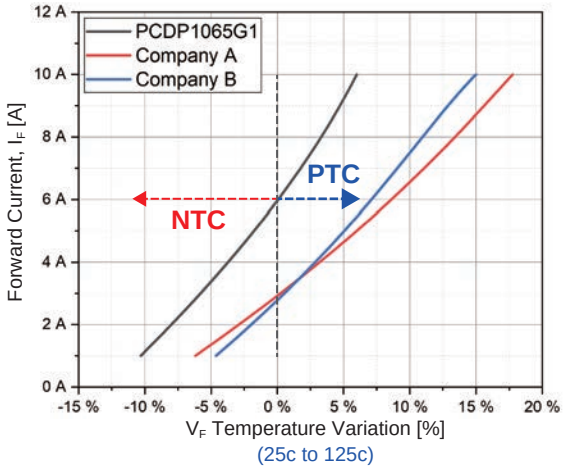
- Home Appliance
- Digital TV

Performance

Temperature coefficient

SiC Diode 650V / 10A

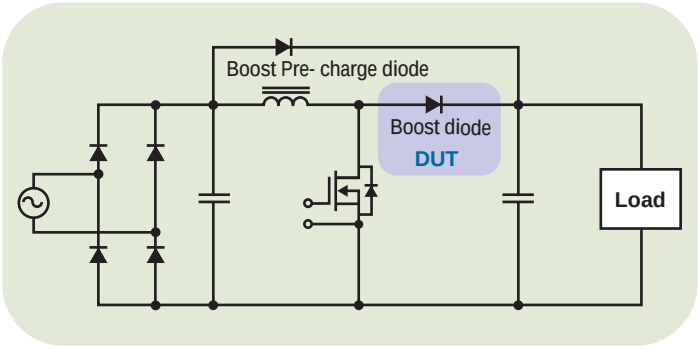


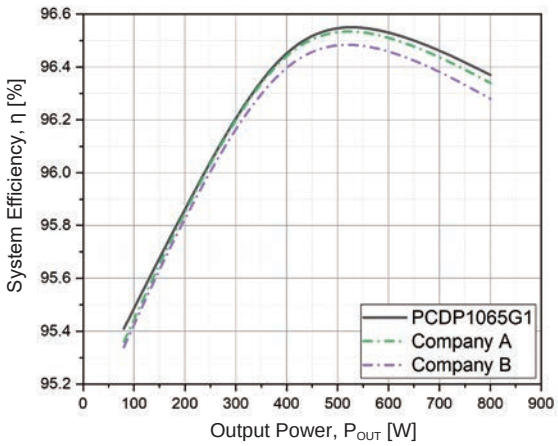


System Evaluation:

800W CCM Boost PFC, Vin = 110Vac/60Hz, Vout = 400V, Fsw = 65kHz

SiC Diode 650V / 10A





SiC SBD Line-Up

Series	BV (V)	I_f (A)	V_f Typ. (V)	C_J (pF)	TO-220AC	TO-263
SiC Diode 650V	650	4	1.5	6	PCDP0465G1	PCDB0465G1
		6	1.5	13	PCDP0665G1	PCDB0665G1
		8	1.5	19	PCDP0865G1	PCDB0865G1
		10	1.5	27	PCDP1065G1	PCDB1065G1
		12	1.5	34	PCDP1265G1	
		16	1.5	48	PCDP1665G1	
		20	1.5	63	PCDP2065G1	
SiC Diode 1200V	1200	5	1.5	13	PCDP05120G1	
		8	1.5	27	PCDP08120G1	
		10	1.5	37	PCDP10120G1	PCDB10120G1
		15	1.5	59	PCDP15120G1	
		20	1.5	78	PCDP20120G1	PCDB20120G1

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